

ABSTRACT

A nitride-based semiconductor light-emitting device having excellent reliability and long lifetime, and a method of manufacturing the same are provided. A nitride-based semiconductor light-emitting element chip, in which a nitride-based semiconductor layer and a first electrode (211) are formed on a surface of an electrically conductive substrate and a second electrode (212) is formed on a rear surface of the electrically conductive substrate, is mounted on a submount (103), and the submount (103) having the nitride-based semiconductor light-emitting element chip mounted thereon is further mounted on a stem (105) to form a nitride-based semiconductor light-emitting device.